

Gyuchull Han

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

416
citations

1163117

8
h-index

1372567

10
g-index

10
all docs

10
docs citations

10
times ranked

981
citing authors

#	ARTICLE	IF	CITATIONS
1	Nano-patterning on multilayer MoS ₂ via block copolymer lithography for highly sensitive and responsive phototransistors. <i>Communications Materials</i> , 2021, 2, .	6.9	19
2	Photoresponse of MoSe ₂ Transistors: A Fully Numerical Quantum Transport Simulation Study. <i>ACS Applied Electronic Materials</i> , 2020, 2, 3765-3772.	4.3	5
3	Ultrasensitive Multilayer MoS ₂ -Based Photodetector with Permanently Grounded Gate Effect. <i>Advanced Electronic Materials</i> , 2020, 6, 1901256.	5.1	14
4	Interstitial Mo-Assisted Photovoltaic Effect in Multilayer MoSe ₂ Phototransistors. <i>Advanced Materials</i> , 2018, 30, e1705542.	21.0	48
5	Label-Free and Recalibrated Multilayer MoS ₂ Biosensor for Point-of-Care Diagnostics. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 43490-43497.	8.0	62
6	Highly Crystalline CVD-grown Multilayer MoSe ₂ Thin Film Transistor for Fast Photodetector. <i>Scientific Reports</i> , 2015, 5, 15313.	3.3	129
7	Giant Photoamplification in Indirect-Bandgap Multilayer MoS ₂ Phototransistors with Local Bottom-Gate Structures. <i>Advanced Materials</i> , 2015, 27, 2224-2230.	21.0	109
8	Phototransistors: Giant Photoamplification in Indirect-Bandgap Multilayer MoS ₂ Phototransistors with Local Bottom-Gate Structures (<i>Adv. Mater.</i> 13/2015). <i>Advanced Materials</i> , 2015, 27, 2126-2126.	21.0	4
9	Scaling Limit of Bilayer Phosphorene FETs. <i>IEEE Electron Device Letters</i> , 2015, 36, 978-980.	3.9	17
10	Contact-dependent performance variability of monolayer MoS ₂ field-effect transistors. <i>Applied Physics Letters</i> , 2014, 105, 213508.	3.3	9